

[ABSTRACT]

With the aim to obtain a phase shift mask with improved dimension and wherein an undercut does not occur in a lower layer light shielding film when the phase shift mask is fabricated, the present phase shift mask blank includes, on a substrate transparent to an exposure wavelength, a phase shift film having resistance to oxygen-containing chlorine-based etching (Cl/O based) and non-oxygen-containing chlorine-based etching (Cl based) and is capable of being etched by fluorine-based etching (F based), a light shielding film having resistance to oxygen-containing chlorine-based etching (Cl/O based) and is capable of being etched by non-oxygen-containing chlorine-based etching (Cl based), and an etching mask film having resistance to fluorine-based etching (F based) and non-oxygen-containing chlorine-based etching (Cl based) and is capable of being etched by oxygen-containing chlorine-based etching (Cl/O based), which are laminated in a named order, and wherein an etching stopper layer is not arranged between the phase shift film and the substrate.